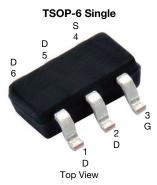




www.vishay.com

# Automotive P-Channel 40 V (D-S) 175 °C MOSFET



Marking Code: 9L

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	-40				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.058				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.092				
I <sub>D</sub> (A)	-6.9				
Configuration	Single				

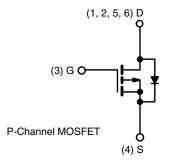
#### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>q</sub> and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



ORDERING INFORMATION	
Package	TSOP-6
Lead (Pb)-free and halogen-free	SQ3419CEV (for detailed order number please see <a href="https://www.vishay.com/doc?79771">www.vishay.com/doc?79771</a> )

ABSOLUTE MAXIMUM RATING	<b>S</b> (T <sub>C</sub> = 25 °C, unles	s otherwise noted	d)		
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage	$V_{DS}$	-40	V		
Gate-source voltage	$V_{GS}$	± 20	V		
Continuous drain current	T <sub>C</sub> = 25 °C	1	-6.9		
Continuous drain current	T <sub>C</sub> = 125 °C	- I <sub>D</sub>	-4		
Continuous source current (diode conductio	I <sub>S</sub>	-6.3	Α		
Pulsed drain current <sup>a</sup>	I <sub>DM</sub>	-27			
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	-16.5		
Single pulse avalanche energy	L=0.1 IIII	E <sub>AS</sub>	13.6	mJ	
Maximum power dissipation	T <sub>C</sub> = 25 °C	ם	5	W	
	T <sub>C</sub> = 125 °C	$P_{D}$	1.6	VV	
Operating junction and storage temperature	range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-ambient	PCB mount b	$R_{thJA}$	110	°C/W	
Junction-to-foot (drain)		$R_{thJF}$	30	C/VV	

#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. When mounted on 1" square PCB (FR4 material)



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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static					•		
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		-40	-	-	V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-1.5	-2.0	-2.5	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
		$V_{GS} = 0 V$	$V_{DS} = -40 \text{ V}$	1	-	-1	
Zero gate voltage drain current	$I_{DSS}$	$V_{GS} = 0 V$	$V_{DS} = -40 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$	ī	-	-50	μΑ
		$V_{GS} = 0 V$	$V_{DS} = -40 \text{ V}, T_{J} = 175 ^{\circ}\text{C}$	-	-	-150	
On-state drain current <sup>a</sup>	$I_{D(on)}$	V <sub>GS</sub> = -10 V	$V_{DS} = -5 V$	-10	-	-	Α
		V <sub>GS</sub> = -10 V	$I_D = -2.5 \text{ A}$	-	0.048	0.058	
Drain-source on-state resistance <sup>a</sup>	D	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -2.5 A, T <sub>J</sub> = 125 °C	-	0.075	-	Ω
Diain-source on-state resistance -	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V	$I_D = -2.5 \text{ A}, T_J = 175 ^{\circ}\text{C}$	-	0.086	-	
		$V_{GS} = -4.5 \text{ V}$	$I_D = -2 A$	-	0.076	0.092	
Forward transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> :	= -20 V, I <sub>D</sub> = -4 A	=.	8	-	S
Dynamic <sup>b</sup>							
Input capacitance	C <sub>iss</sub>			-	745	990	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{DS} = -20 \text{ V}, f = 1 \text{ MHz}$	-	134	180	рF
Reverse transfer capacitance	C <sub>rss</sub>			-	83	100	
Total gate charge <sup>c</sup>	Qg			-	8.35	11.3	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	$V_{GS} = -4.5 \text{ V}$	$V_{DS} = -20 \text{ V}, I_{D} = -4 \text{ A}$	-	2.9	-	nC
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	4.0	-	
Gate resistance	Rg		f = 1 MHz		5.7	7.9	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	8	12	
Rise time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> :	$V_{DD} = -20 \text{ V}, R_1 = 5 \Omega$		24	36	- ns
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \simeq -4$ Å, $V_{GEN} = -10$ V, $R_g = 1$ $\Omega$		-	26	39	
Fall time <sup>c</sup>	t <sub>f</sub>			-	31	47	
Source-Drain Diode Ratings and Charac	teristics <sup>b</sup>						
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	-27	Α
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> = -1.6 A, V <sub>GS</sub> = 0 V		-	-0.8	-1.2	V
Body diode reverse recovery time	t <sub>rr</sub>			-	24	48	ns
Body diode reverse recovery charge	Q <sub>rr</sub>	I <sub>F</sub> = -3 A, di/dt = 100 A/μs		-	23	46	nC
Reverse recovery fall time	ta			-	16	-	
Reverse recovery rise time	t <sub>b</sub>			-	8	-	ns
Body diode peak reverse recovery current	I <sub>RM(REC)</sub>			-	-2.17	-	Α

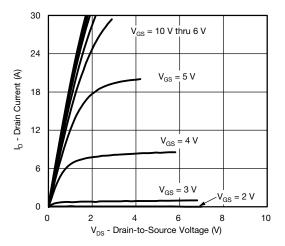
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

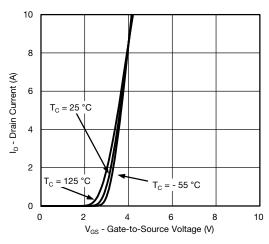
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



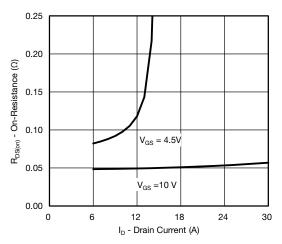
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



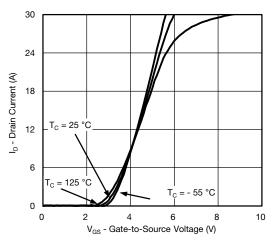
#### **Output Characteristics**



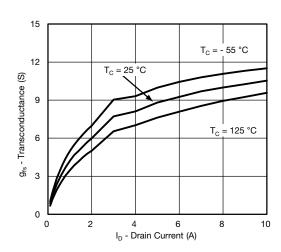
**Transfer Characteristics** 



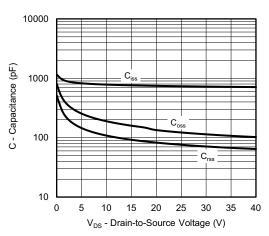
On-Resistance vs. Drain Current



**Transfer Characteristics** 



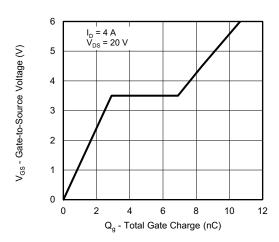
Transconductance



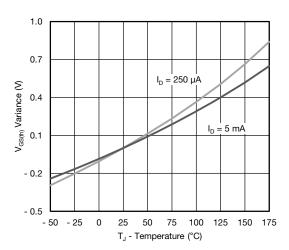
Capacitance



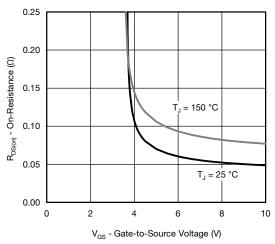
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



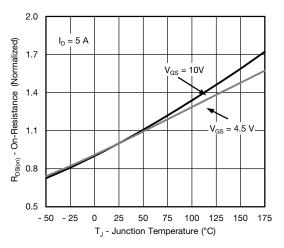
#### **Gate Charge**



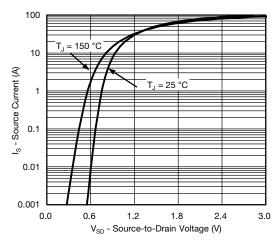
#### **Threshold Voltage**



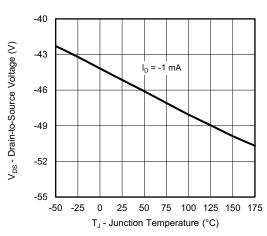
On-Resistance vs. Gate-to-Source Voltage



On-Resistance vs. Junction Temperature



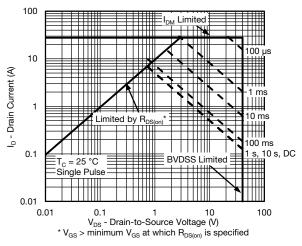
Source Drain Diode Forward Voltage



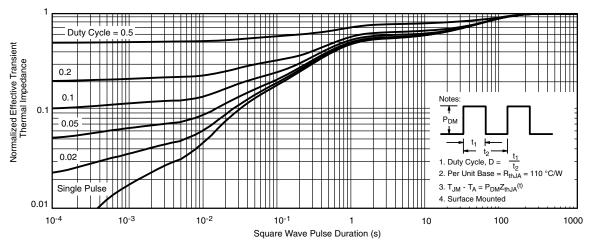
**Drain Source Breakdown vs. Junction Temperature** 



### **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



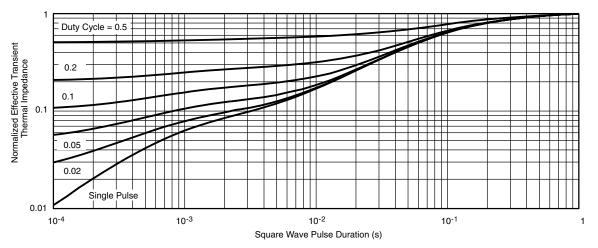
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

can widely vary depending on actual application parameters and operating conditions

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?62368">www.vishay.com/ppg?62368</a>.





TSOP: 5/6-LEAD

**JEDEC Part Number: MO-193C** 





**5-LEAD TSOP** 







	MIL	LIMETER	RS	INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.91	-	1.10	0.036	-	0.043	
A <sub>1</sub>	0.01	-	0.10	0.0004	-	0.004	
A <sub>2</sub>	0.90	-	1.00	0.035	0.038	0.039	
b	0.30	0.32	0.45	0.012	0.013	0.018	
С	0.10	0.15	0.20	0.004 0.006 0		0.008	
D	2.95	3.05	3.10	0.116	0.120	0.122	
E	2.70	2.85	2.98	0.106	0.112	0.117	
E <sub>1</sub>	1.55	1.65	1.70	0.061	0.065	0.067	
е		0.95 BSC		0.0374 BSC			
e <sub>1</sub>	1.80	1.90	2.00	0.071 0.075 0.		0.079	
L	0.32	-	0.50	0.012	-	0.020	
L <sub>1</sub>		0.60 Ref		0.024 Ref			
L <sub>2</sub>		0.25 BSC		0.010 BSC			
R	0.10	-	-	0.004	-	-	
θ	0°	4°	8°	0°	4°	8°	
θ1		7° Nom	om 7° Nom				
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540							

DWG: 5540

Document Number: 71200 18-Dec-06



## Recommended Land Pattern For TSOP-5L / TSOP-6L



### Note

• All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022 DWG: 3010



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